

PDP SWITCH

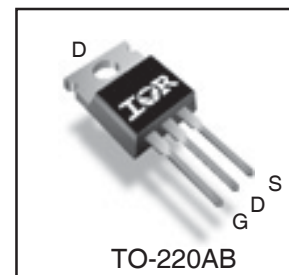
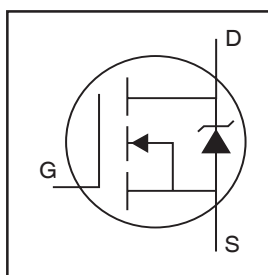
IRFB4228PbF

Features

- Advanced Process Technology
- Key Parameters Optimized for PDP Sustain, Energy Recovery and Pass Switch Applications
- Low E_{PULSE} Rating to Reduce Power Dissipation in PDP Sustain, Energy Recovery and Pass Switch Applications
- Low Q_G for Fast Response
- High Repetitive Peak Current Capability for Reliable Operation
- Short Fall & Rise Times for Fast Switching
- 175°C Operating Junction Temperature for Improved Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability

Key Parameters

$V_{DS\ min}$	150	V
$V_{DS\ (Avalanche)\ typ.}$	180	V
$R_{DS(ON)\ typ.\ @\ 10V}$	12	mΩ
$I_{RP\ max\ @\ T_C = 100^\circ C}$	170	A
$T_J\ max$	175	°C



G	D	S
Gate	Drain	Source

Description

This HEXFET® Power MOSFET is specifically designed for Sustain; Energy Recovery & Pass switch applications in Plasma Display Panels. This MOSFET utilizes the latest processing techniques to achieve low on-resistance per silicon area and low E_{PULSE} rating. Additional features of this MOSFET are 175°C operating junction temperature and high repetitive peak current capability. These features combine to make this MOSFET a highly efficient, robust and reliable device for PDP driving applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{GS}	Gate-to-Source Voltage	±30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	83	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	59	
I_{DM}	Pulsed Drain Current ①	330	
$I_{RP} @ T_C = 100^\circ C$	Repetitive Peak Current ⑤	170	
$P_D @ T_C = 25^\circ C$	Power Dissipation	330	W
$P_D @ T_C = 100^\circ C$	Power Dissipation	170	
	Linear Derating Factor	2.2	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-40 to + 175	°C
	Soldering Temperature for 10 seconds	300	
	Mounting Torque, 6-32 or M3 Screw	10lb·in (1.1N·m)	N

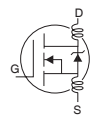
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	0.45	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ④	—	62	

Notes ① through ⑤ are on page 8

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	150	—	mV/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	12	15	m Ω	$V_{GS} = 10V, I_D = 33A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-14	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	1.0	mA	$V_{DS} = 150V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$
g_{fs}	Forward Transconductance	170	—	—	S	$V_{DS} = 25V, I_D = 50A$
Q_g	Total Gate Charge	—	71	107	nC	$V_{DD} = 75V, I_D = 50A, V_{GS} = 10V$ ③
Q_{gd}	Gate-to-Drain Charge	—	21	—	nC	
$t_{d(on)}$	Turn-On Delay Time	—	18	—	ns	$V_{DD} = 75V, V_{GS} = 10V$ ③ $I_D = 50A$ $R_G = 2.5\Omega$ See Fig. 22
t_r	Rise Time	—	59	—		
$t_{d(off)}$	Turn-Off Delay Time	—	24	—		
t_f	Fall Time	—	33	—		
t_{st}	Shoot Through Blocking Time	100	—	—	ns	$V_{DD} = 120V, V_{GS} = 15V, R_G = 5.1\Omega$
E_{PULSE}	Energy per Pulse	—	58	—	μJ	$L = 220nH, C = 0.3\mu F, V_{GS} = 15V$ $V_{DS} = 120V, R_G = 5.1\Omega, T_J = 25^\circ\text{C}$
		—	110	—		$L = 220nH, C = 0.3\mu F, V_{GS} = 15V$ $V_{DS} = 120V, R_G = 5.1\Omega, T_J = 100^\circ\text{C}$
C_{iss}	Input Capacitance	—	4530	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	550	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	100	—		$f = 1.0MHz$
$C_{oss, eff.}$	Effective Output Capacitance	—	480	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 120V$
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		

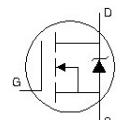


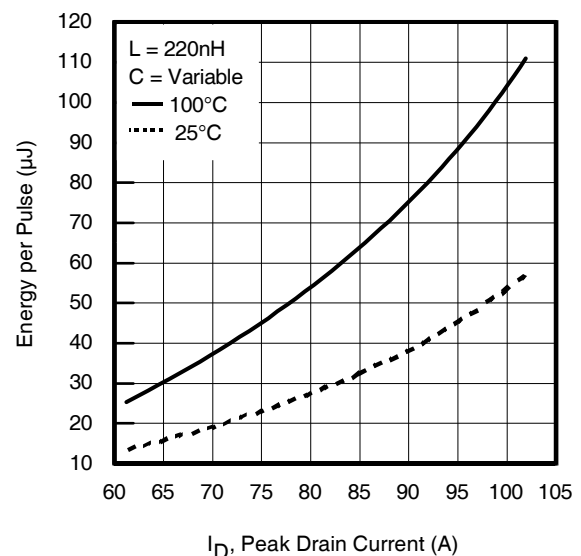
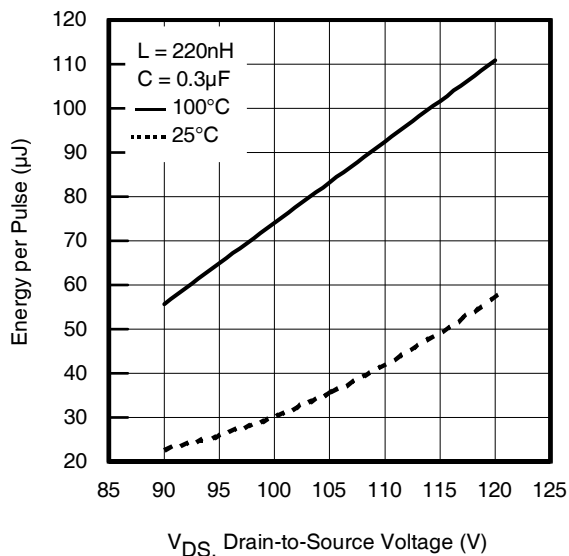
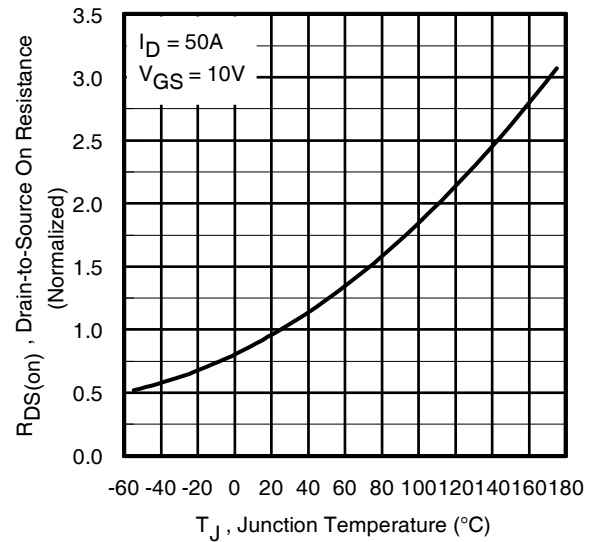
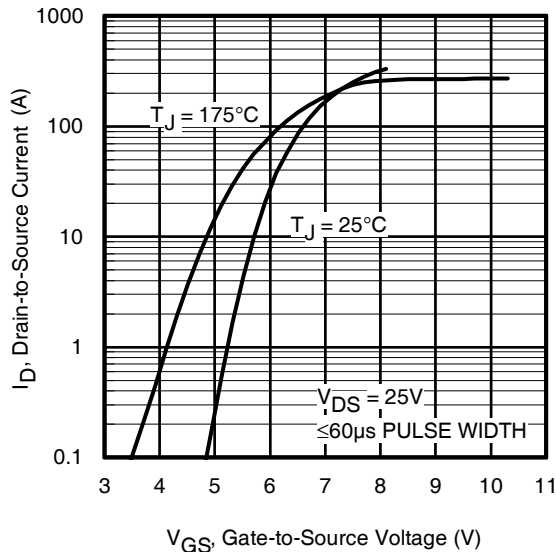
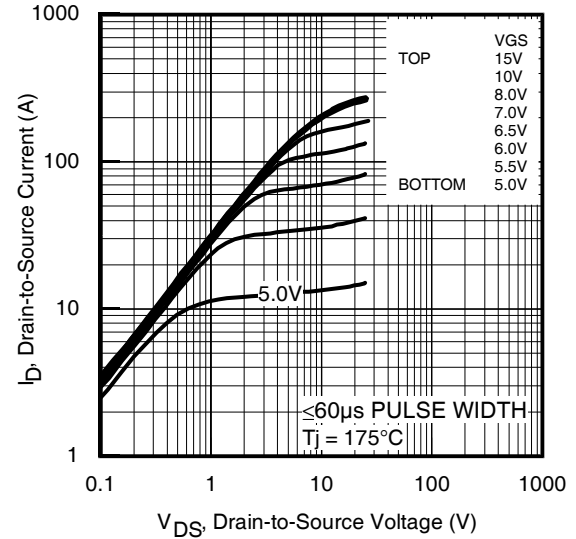
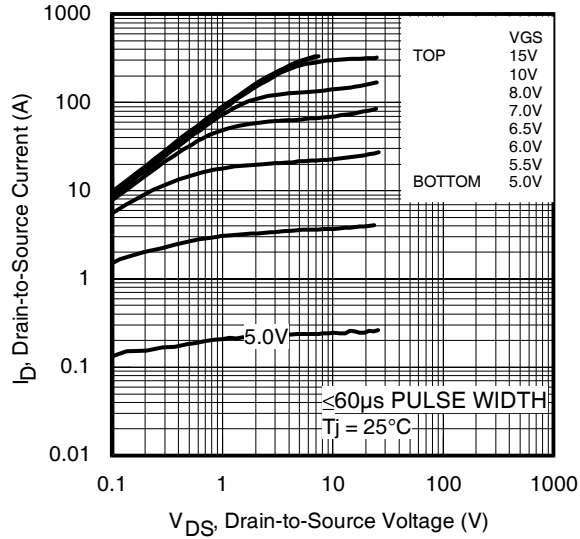
Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	120	mJ
E_{AR}	Repetitive Avalanche Energy ①	—	33	mJ
$V_{DS(Avalanche)}$	Repetitive Avalanche Voltage ①	180	—	V
I_{AS}	Avalanche Current ②	—	50	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	83	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	330		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 50A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	76	110	ns	$T_J = 25^\circ\text{C}, I_F = 50A, V_{DD} = 50V$
Q_{rr}	Reverse Recovery Charge	—	230	350	nC	$di/dt = 100A/\mu s$ ③





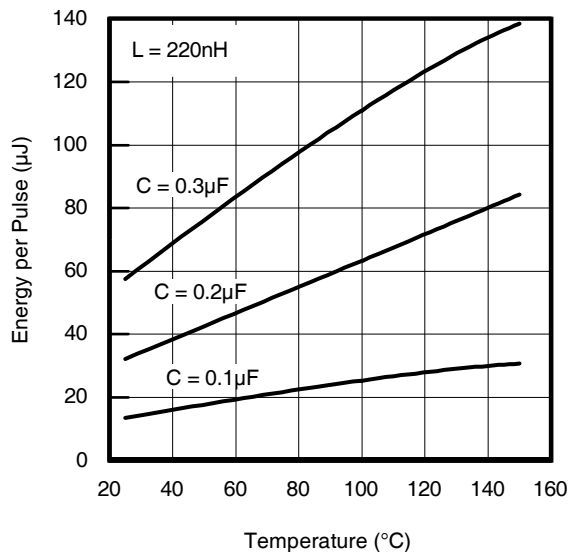


Fig 7. Typical E_{PULSE} vs. Temperature

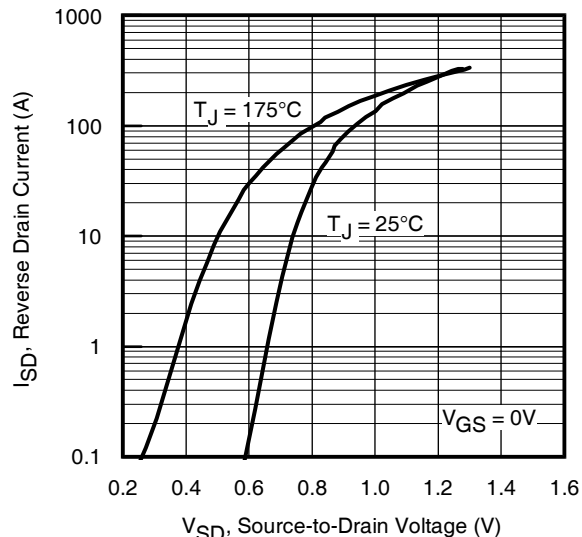


Fig 8. Typical Source-Drain Diode Forward Voltage

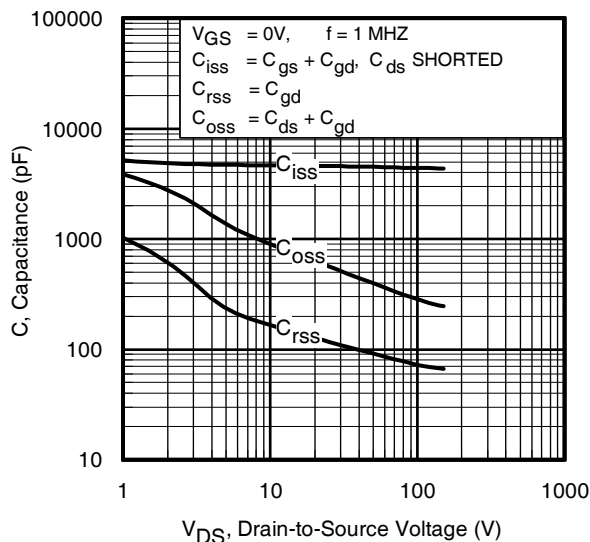


Fig 9. Typical Capacitance vs. Drain-to-Source Voltage

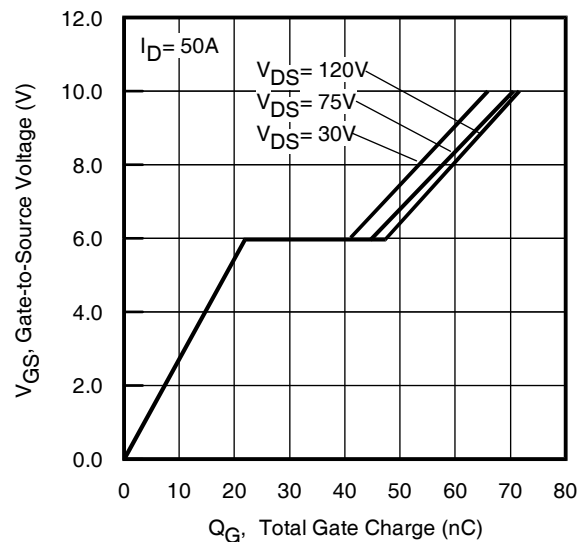


Fig 10. Typical Gate Charge vs. Gate-to-Source Voltage

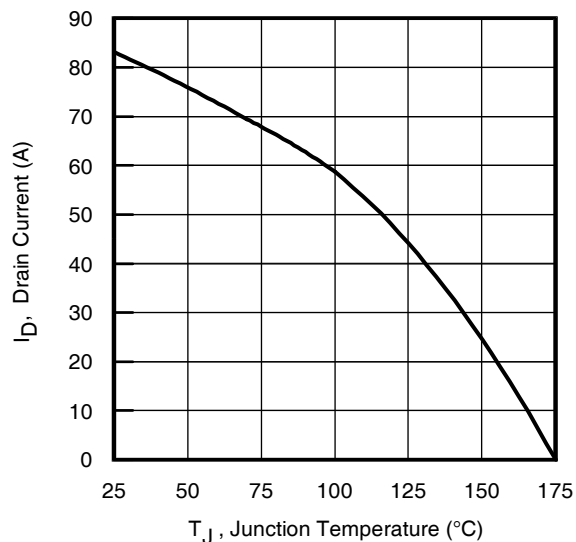


Fig 11. Maximum Drain Current vs. Case Temperature

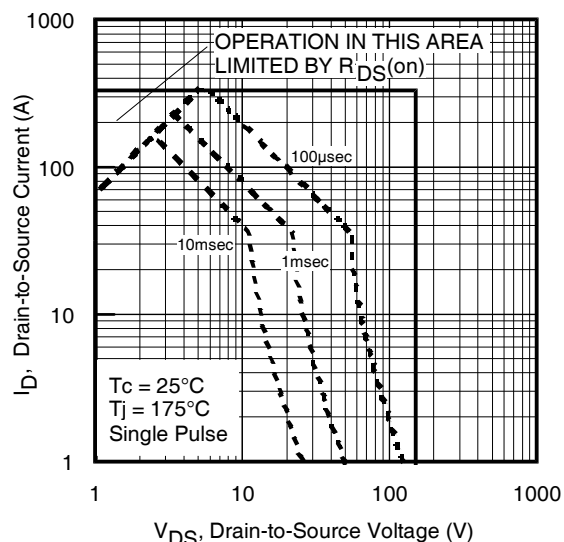


Fig 12. Maximum Safe Operating Area

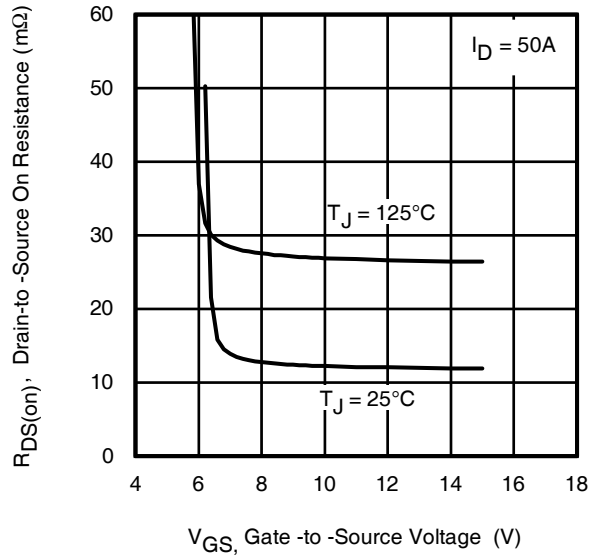


Fig 13. On-Resistance vs. Gate Voltage

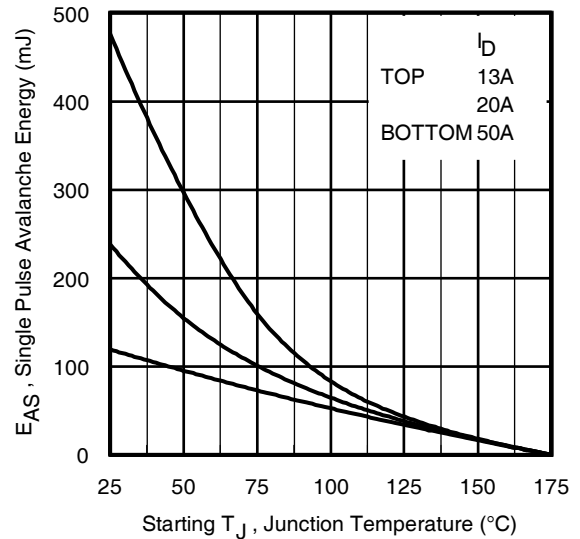


Fig 14. Maximum Avalanche Energy vs. Temperature

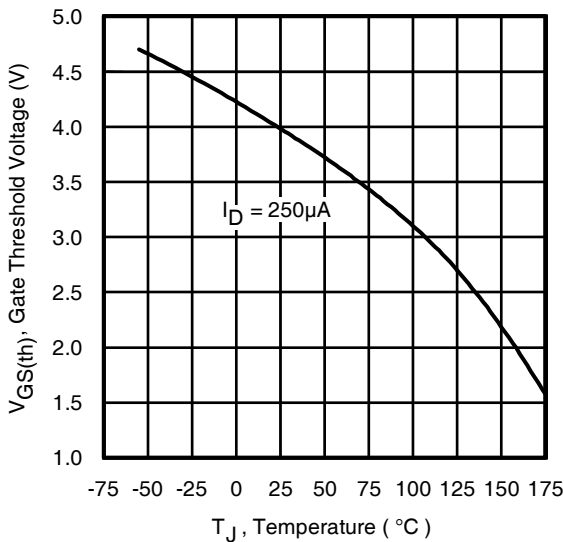


Fig 15. Threshold Voltage vs. Temperature

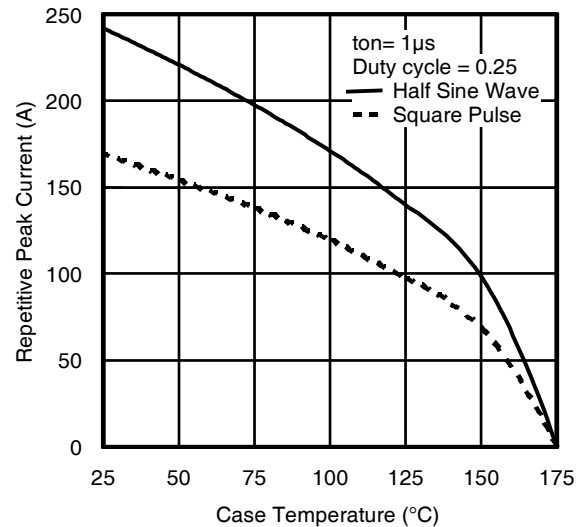


Fig 16. Typical Repetitive peak Current vs. Case temperature

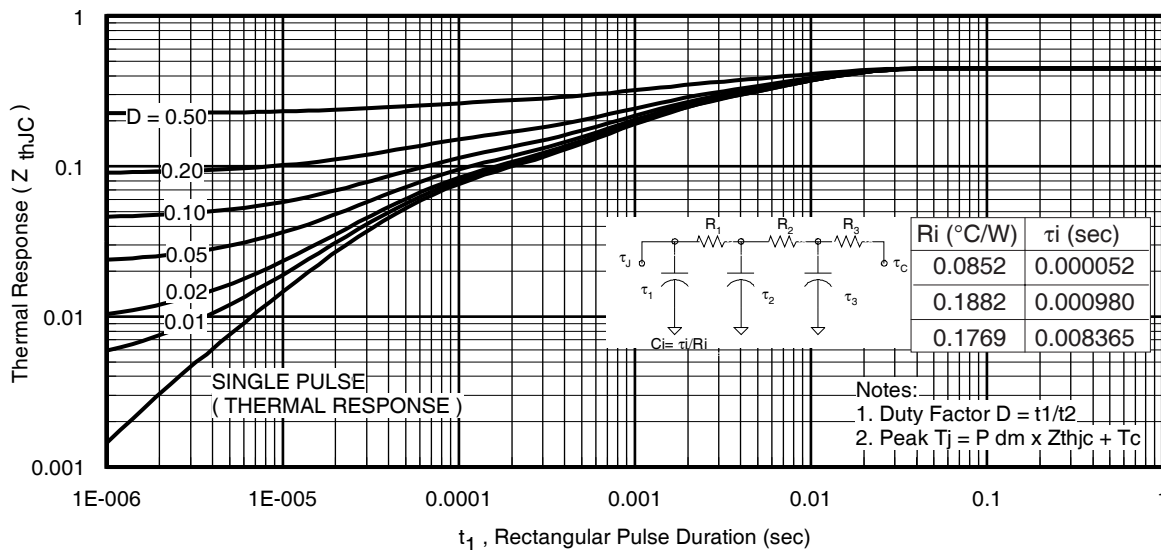


Fig 17. Maximum Effective Transient Thermal Impedance, Junction-to-Case

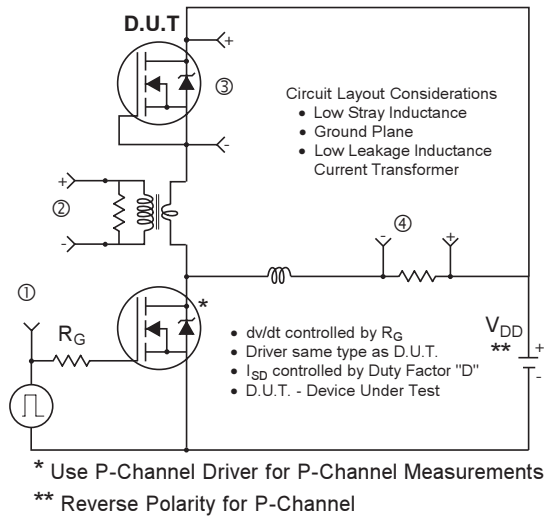


Fig 18. Diode Reverse Recovery Test Circuit for HEXFET® Power MOSFETs

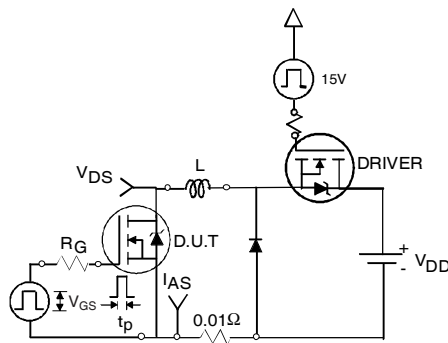
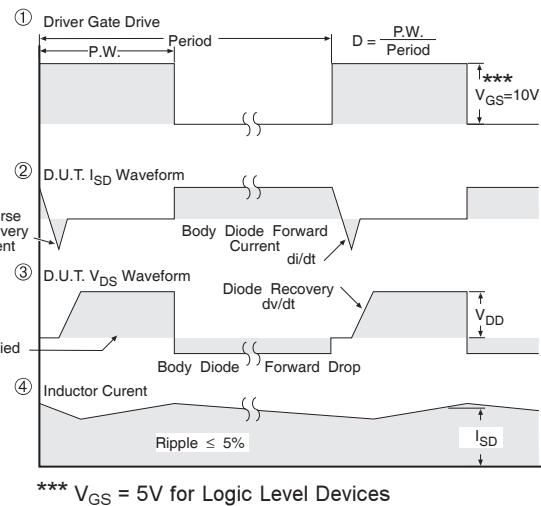


Fig 19a. Unclamped Inductive Test Circuit

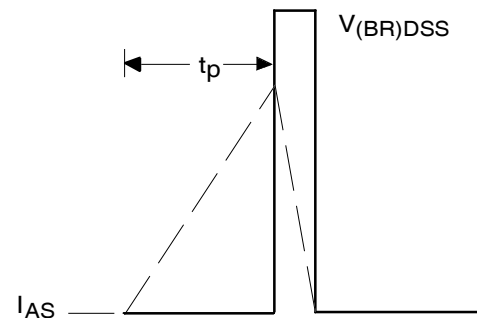


Fig 19b. Unclamped Inductive Waveforms

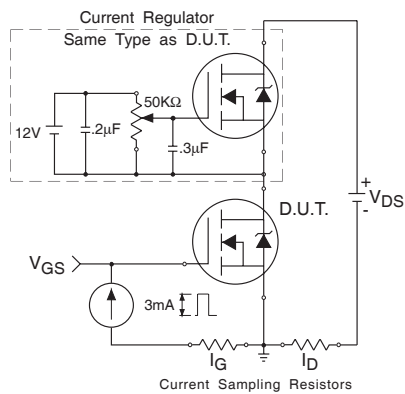


Fig 20a. Gate Charge Test Circuit

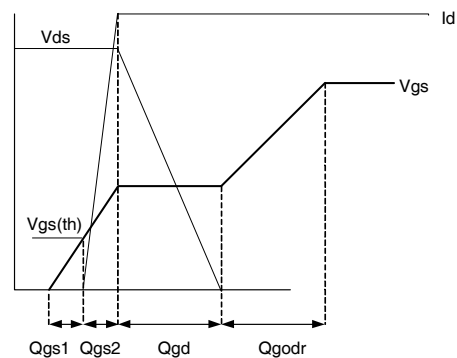


Fig 20b. Gate Charge Waveform

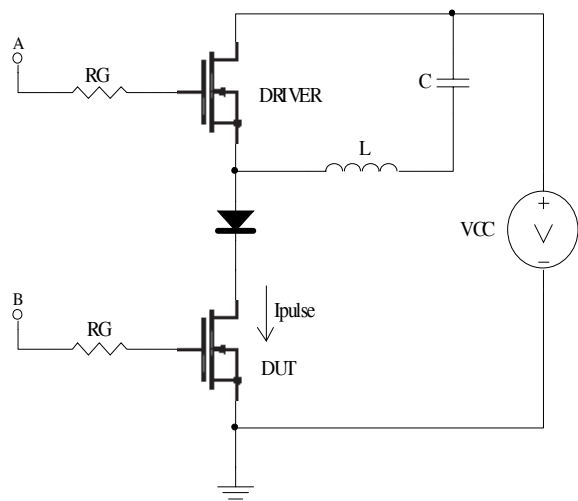


Fig 21a. t_{st} and E_{PULSE} Test Circuit

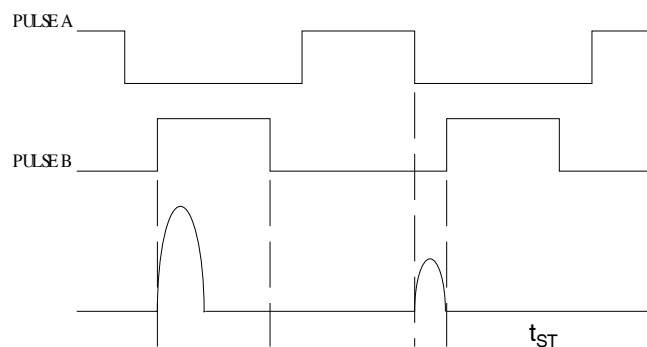


Fig 21b. t_{st} Test Waveforms

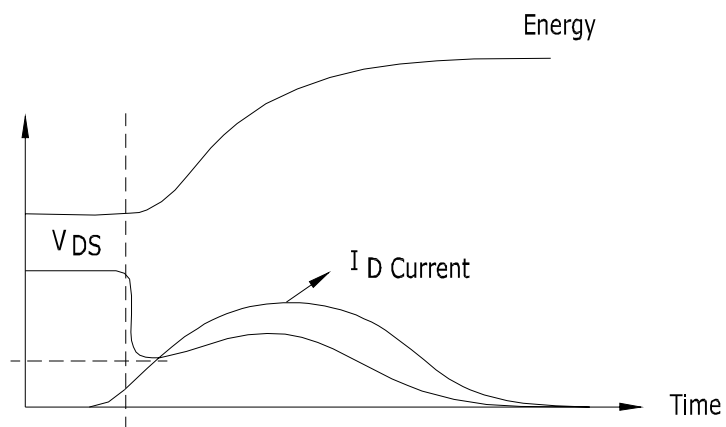


Fig 21c. E_{PULSE} Test Waveforms

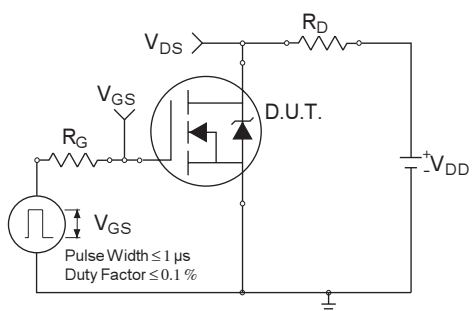


Fig 22a. Switching Time Test Circuit

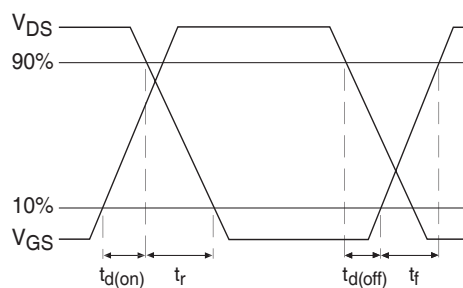


Fig 22b. Switching Time Waveforms

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Figure 1: Dimensions and details of the test specimen. The figure includes three views: a top view, a side view, and a cross-sectional view. The top view shows a rectangular base with a central circular feature and three vertical pins. Dimensions include E (width), D (height), D1 (height to pins), L1 (pin length), L (total length), and 2X (pin spacing). A detail B is shown as a circular inset. The side view shows the profile of the specimen with dimensions A, A1, A2, H1, and C. A detail B is also shown. The cross-sectional view shows the internal structure with dimensions b1, b2, c1, c, and b3. A detail B is shown as a circular inset. The figure is labeled 'VIEW A-A' and 'SECTION C-C & D-D'.

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	5
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	
b2	1.15	1.77	.045	.070	5
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	
D	14.22	16.51	.560	.650	
D1	8.38	9.02	.330	.355	7
D2	12.19	12.88	.480	.507	
E	9.66	10.66	.380	.420	
E1	8.38	8.89	.330	.350	4,7
e	2.54 BSC		.100 BSC		7,8
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	
L	12.70	14.73	.500	.580	3
L1	-	6.35	-	.250	
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°-93°		90°-93°		

Diagram of an IRF1010 MOSFET package with the following labels:

- INTERNATIONAL RECTIFIER LOGO
- PART NUMBER
- DATE CODE
- YEAR 0 = 2000
- WEEK 19
- LINE C
- ASSEMBLY LOT CODE

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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